

IGBT - Field Stop

600 V, 40 A

FGH80N60FD2

Description

Using novel field stop IGBT technology, ON Semiconductor's field stop IGBTs offer the optimum performance for induction heating and PFC applications where low conduction and switching losses are essential.

Features

- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.8 \text{ V (Typ.) @ } I_C = 40 \text{ A}$
- High Input Impedance
- Fast Switching
- This Device is Pb-Free and is RoHS Compliant

Applications

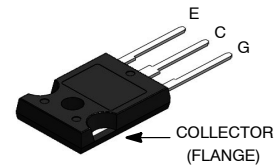
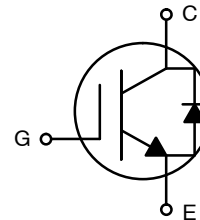
- Induction Heating, PFC



ON Semiconductor®

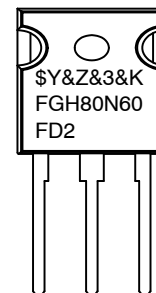
www.onsemi.com

V_{CES}	I_C
600 V	40 A



TO-247-3LD
CASE 340CK

MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FGH80N60FD2	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FGH80N60FD2

ABSOLUTE MAXIMUM RATINGS

Symbol	Description	Ratings	Unit	
V_{CES}	Collector to Emitter Voltage	600	V	
V_{GES}	Gate–Emitter Voltage	± 20	V	
I_C	Collector Current	$T_C = 25^\circ\text{C}$	80	A
		$T_C = 100^\circ\text{C}$	40	A
I_{CM} (Note 1)	Pulsed Collector Current	$T_C = 25^\circ\text{C}$	160	A
P_D	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	290	W
		$T_C = 100^\circ\text{C}$	116	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$	
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: Pulse width limited by max. junction temperature.

THERMAL CHARACTERISTICS

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.43	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$ (Diode)	Thermal Resistance, Junction to Case	-	1.45	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	$^\circ\text{C}/\text{W}$

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH80N60FD2TU	FGH80N60FD2	TO-247	Tube	N/A	N/A	30

ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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OFF CHARACTERISTICS

BV_{CES}	Collector–Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	600	-	-	V
$\Delta BV_{CES} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	-	0.6	-	$\text{V}/^\circ\text{C}$
I_{CES}	Collector Cut–Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	μA
I_{GES}	G–E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	± 400	nA

ON CHARACTERISTICS

$V_{GE(th)}$	G–E Threshold Voltage	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	4.5	5.5	7.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40\text{ A}, V_{GE} = 15\text{ V},$	-	1.8	2.4	V
		$I_C = 40\text{ A}, V_{GE} = 15\text{ V},$ $T_C = 125^\circ\text{C}$	-	2.05	-	V

DYNAMIC CHARACTERISTICS

C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V},$ $f = 1\text{ MHz}$	-	2110	-	pF
C_{oes}	Output Capacitance		-	200	-	pF
C_{res}	Reverse Transfer Capacitance		-	60	-	pF

FGH80N60FD2

ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
SWITCHING CHARACTERISTICS						
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}$, $I_C = 40\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, Inductive Load, $T_C = 25^\circ\text{C}$	–	21	–	ns
T_r	Rise Time		–	56	–	ns
$T_{d(off)}$	Turn-Off Delay Time		–	126	–	ns
T_f	Fall Time		–	50	100	ns
E_{on}	Turn-On Switching Loss		–	1	1.5	mJ
E_{off}	Turn-Off Switching Loss		–	0.52	0.78	mJ
E_{ts}	Total Switching Loss		–	1.52	2.28	mJ
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}$, $I_C = 40\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, Inductive Load, $T_C = 125^\circ\text{C}$	–	20	–	ns
T_r	Rise Time		–	54	–	ns
$T_{d(off)}$	Turn-Off Delay Time		–	131	–	ns
T_f	Fall Time		–	70	–	ns
E_{on}	Turn-On Switching Loss		–	1.1	–	mJ
E_{off}	Turn-Off Switching Loss		–	0.78	–	mJ
E_{ts}	Total Switching Loss		–	1.88	–	mJ
Q_g	Total Gate Charge	$V_{CE} = 400\text{ V}$, $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$	–	120	–	nC
Q_{ge}	Gate-Emitter Charge		–	14	–	nC
Q_{gc}	Gate-Collector Charge		–	58	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS OF THE DIODE ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit	
V_{FM}	Diode Forward Voltage	$I_F = 15\text{ A}$	$T_C = 25^\circ\text{C}$	–	1.2	1.5	V
			$T_C = 125^\circ\text{C}$	–	1.0	–	
T_{rr}	Diode Reverse Recovery Time	$I_F = 15\text{ A}$, $di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	–	61	–	ns
			$T_C = 125^\circ\text{C}$	–	125	–	
I_{rr}	Diode Reverse Recovery Current		$T_C = 25^\circ\text{C}$	–	4.8	–	A
			$T_C = 125^\circ\text{C}$	–	8.4	–	
Q_{rr}	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	–	146	–	nC
			$T_C = 125^\circ\text{C}$	–	525	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS

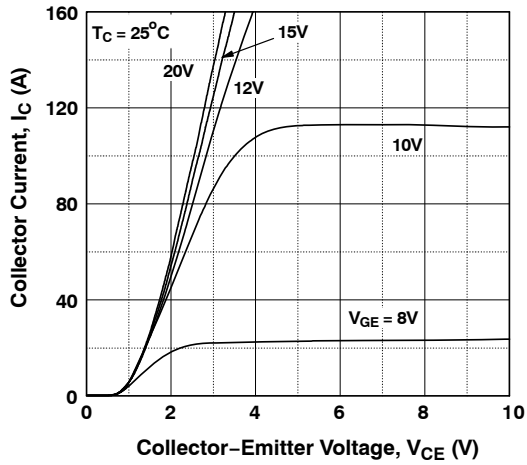


Figure 1. Typical Output Characteristics

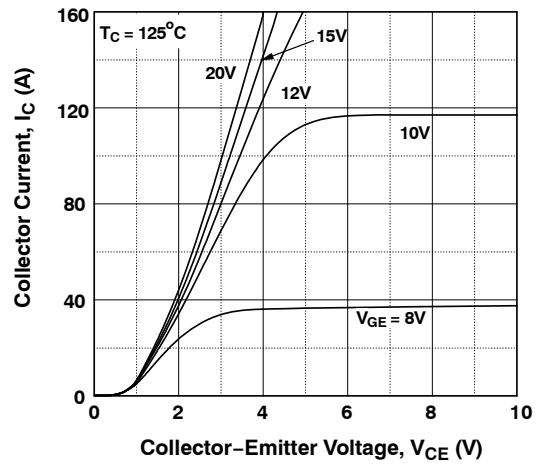


Figure 2. Typical Saturation Voltage Characteristics

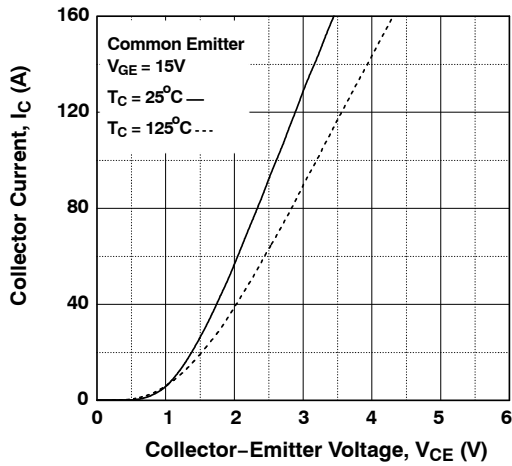


Figure 3. Typical Saturation Voltage Characteristics

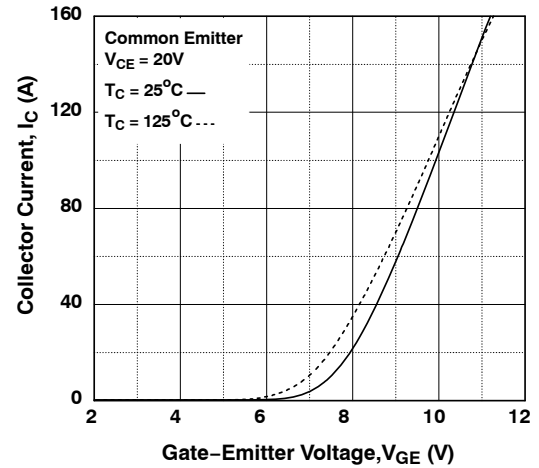


Figure 4. Transfer Characteristics

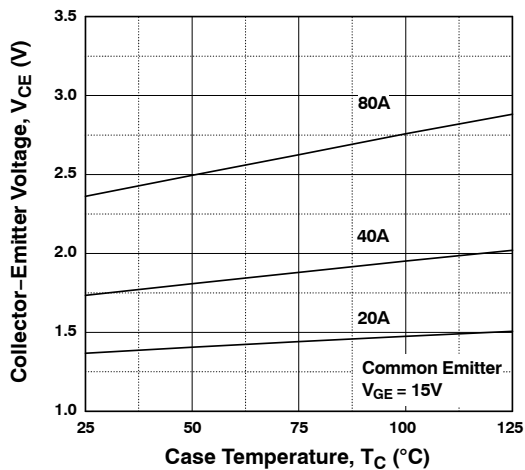


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

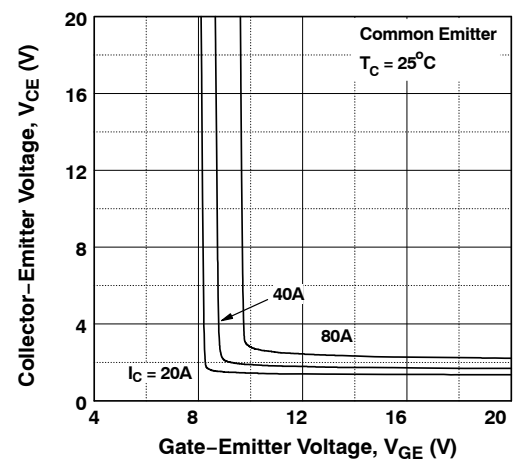


Figure 6. Saturation Voltage vs. V_{GE}

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

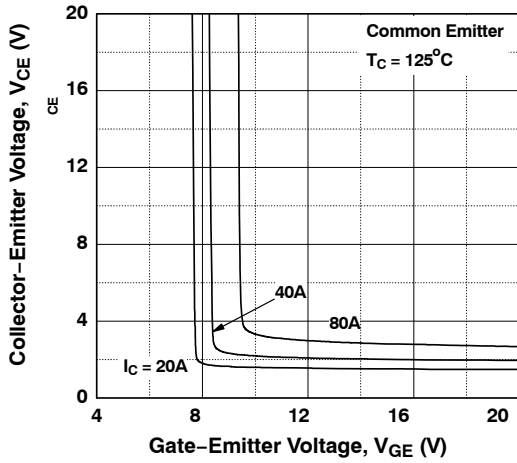


Figure 7. Saturation Voltage vs. V_{GE}

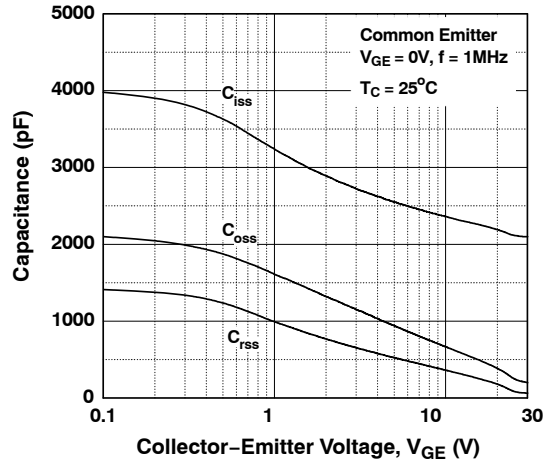


Figure 8. Capacitance Characteristics

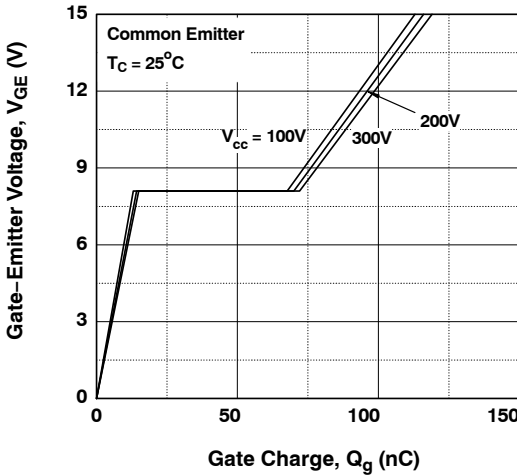


Figure 9. Gate Charge Characteristics

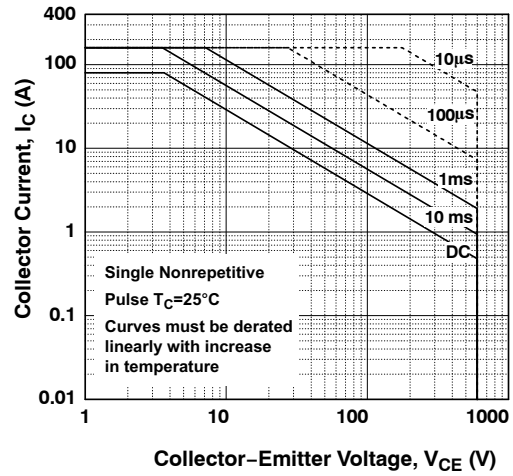


Figure 10. SOA Characteristics

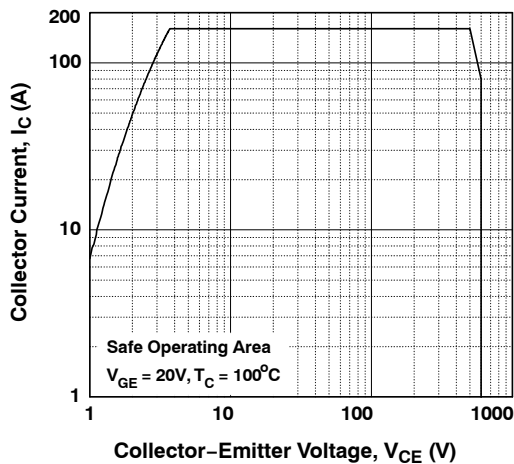


Figure 11. Turn-Off Switching SOA Characteristics

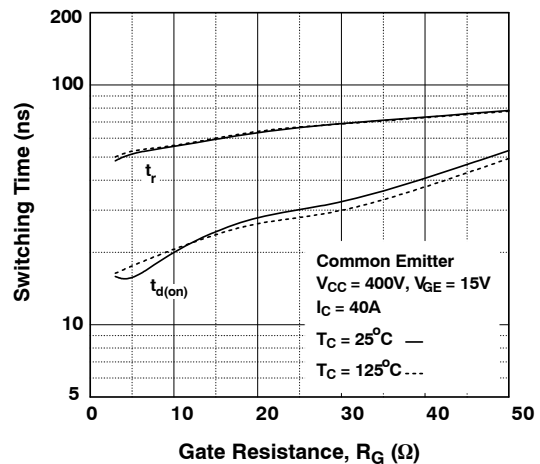


Figure 12. Turn-On Characteristics vs. Gate Resistance

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

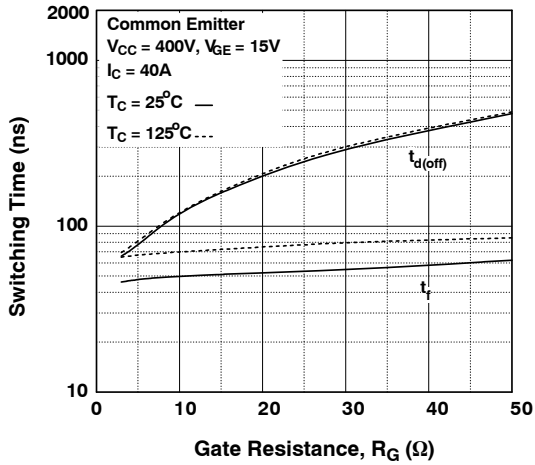


Figure 13. Turn-Off Characteristics vs. Gate Resistance

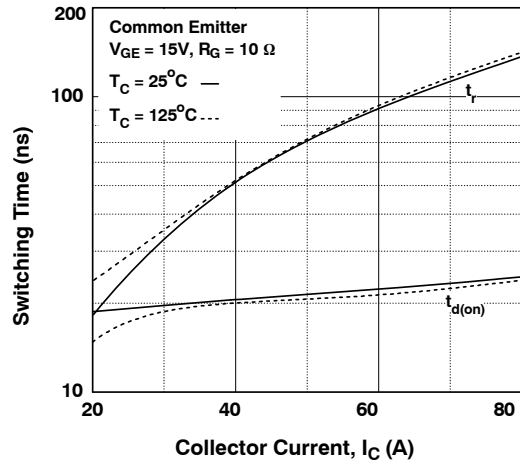


Figure 14. Turn-On Characteristics vs. Collector Current

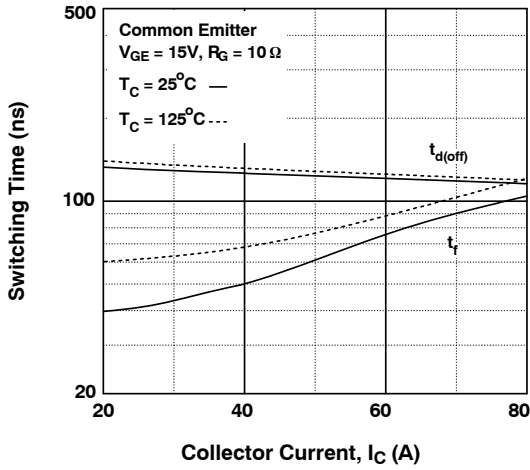


Figure 15. Turn-Off Characteristics vs. Collector Current

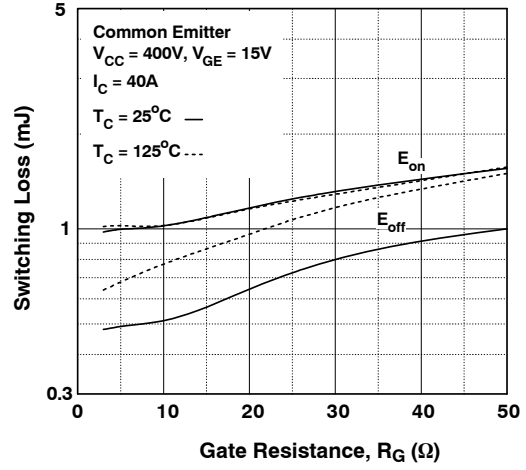


Figure 16. Switching Loss vs. Gate Resistance

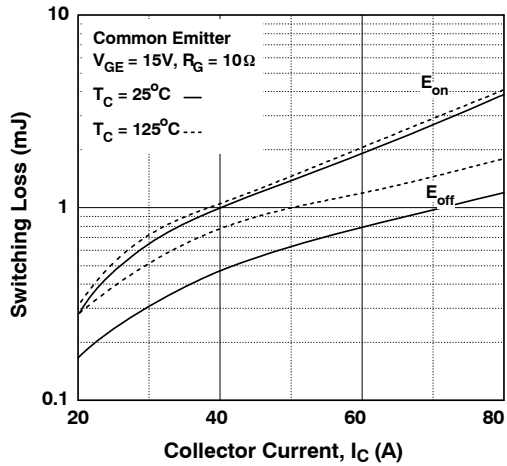


Figure 17. Switching Loss vs. Collector Current

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

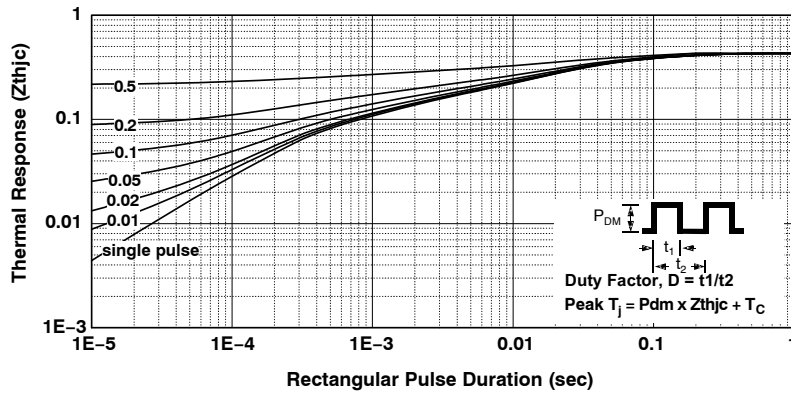


Figure 19. Transient Thermal Impedance of IGBT

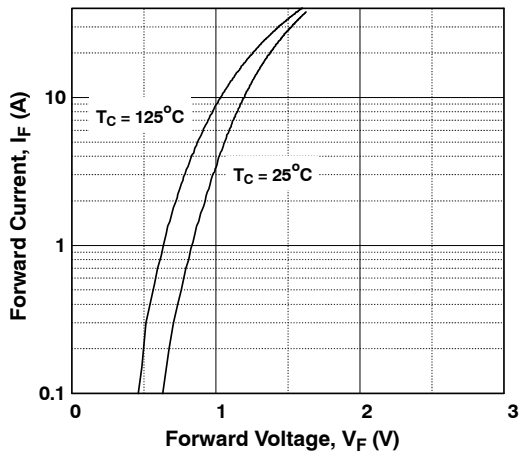


Figure 18. Forward Characteristics

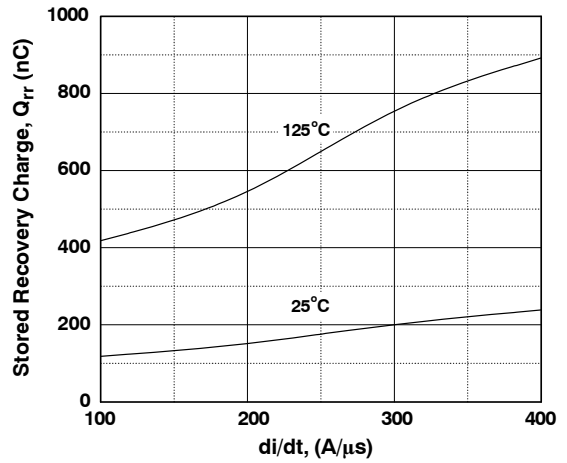


Figure 20. Stored Charge

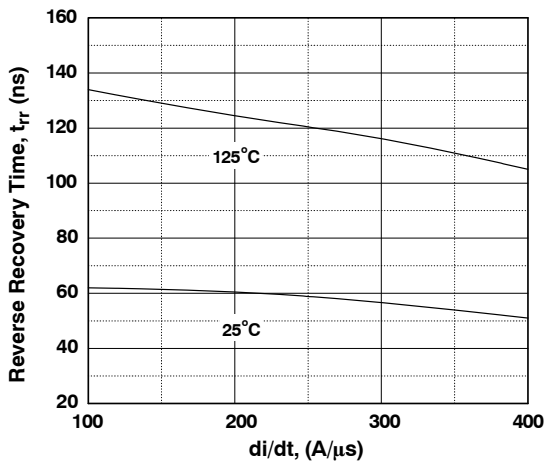


Figure 21. Reverse Recovery Time

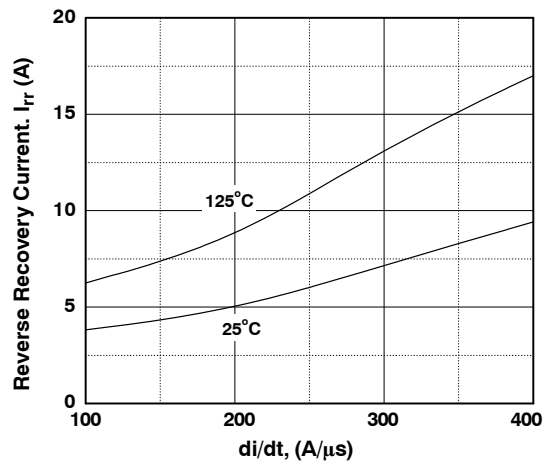


Figure 22. Reverse Recovery Current

TO-247-3LD SHORT LEAD
CASE 340CK
ISSUE A

DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
ØP1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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